



BDX 66, A, B, C

PNP SILICON DARLINGTONS

High current power darlington designed for power amplification and switching applications.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit
V_{CEO}	Collector-Emitter Voltage		BDX66 -60	V
			BDX66A -80	
			BDX66B -100	
			BDX66C -120	
V_{CBO}	Collector-Base Voltage		BDX66 -60	V
			BDX66A -80	
			BDX66B -100	
			BDX66C -120	
V_{EBO}	Emitter-Base Voltage		BDX66 BDX66A BDX66B BDX66C -5.0	V
I_C	Collector Current	$I_{C(RMS)}$	BDX66 BDX66A BDX66B BDX66C -16	A
		I_{CM}	BDX66 BDX66A BDX66B BDX66C -20	
I_B	Base Current		BDX66 BDX66A BDX66B BDX66C -0.25	A
P_T	Power Dissipation	@ $T_C = 25^\circ$	BDX66 BDX66A BDX66B BDX66C 150	Watts W/°C
T_J	Junction Temperature		BDX66 BDX66A BDX66B BDX66C -55 to +200	°C
T_S	Storage Temperature		BDX66 BDX66A BDX66B BDX66C -55 to +200	°C

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THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-C}	Thermal Resistance, Junction to Case BDX66 BDX66A BDX66B BDX66C	1.17	°C/W

ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Mx	Unit	
$V_{CEO(SUS)}$	Collector-Emitter Breakdown Voltage (*)	$I_C = -0.1\text{ A}$, $L = 25\text{mH}$	BDX66	-60	-	-	V
			BDX66A	-80	-	-	
			BDX66B	-100	-	-	
			BDX66C	-120	-	-	
I_{CEO}	Collector Cutoff Current	$V_{CE} = -30\text{ V}$	BDX66	-	-	-3	mA
		$V_{CE} = -40\text{ V}$	BDX66A	-	-		
		$V_{CE} = -50\text{ V}$	BDX66B	-	-		
		$V_{CE} = -60\text{ V}$	BDX66C	-	-		

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Symbol	Ratings	Test Condition(s)	Min	Typ	Mx	Unit
I_{EBO}	Emitter Cutoff Current	$V_{BE}=-5\text{ V}$	-	-	-5.0	mA
I_{CBO}	Collector-Base Cutoff Current	$T_{CASE}=25^{\circ}\text{C}, V_{CB}=-40\text{ V}$	-	-	-1	mA
		----- $T_{CASE}=150^{\circ}\text{C}$	-	-	-5	
		$T_{CASE}=25^{\circ}\text{C}, V_{CB}=-50\text{ V}$	-	-	-1	
		----- $T_{CASE}=150^{\circ}\text{C}$	-	-	-5	
		$T_{CASE}=25^{\circ}\text{C}, V_{CB}=-60\text{ V}$	-	-	-1	
		----- $T_{CASE}=150^{\circ}\text{C}$	-	-	-5	
		$T_{CASE}=25^{\circ}\text{C}, V_{CB}=-70\text{ V}$	-	-	-1	
		----- $T_{CASE}=150^{\circ}\text{C}$	-	-	-5	
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C=-10\text{ A}, I_B=-40\text{ mA}$	-	-	-2	V
C_{22b}		$I_E=0\text{ A}, V_{CB}=-10\text{ V}, f=1\text{ MHz}$	-	300	-	pF
t_{on}	Switching characteristics	$V_{CC}=12\text{ V}, I_C=-10\text{ A}, I_{B1}=-I_{B2}=0.04$	-	1	-	μs
t_{off}			-	3.5	-	

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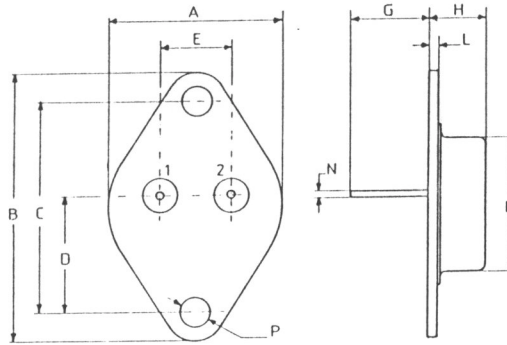
Symbol	Ratings	Test Condition(s)	Min	Typ	Mx	Unit
f_c		$V_{CE} = -3 \text{ V}$, $I_C = -5 \text{ A}$, $f = 1 \text{ MHz}$	-	60	-	kHz

(*) Pulse Width $\approx 300 \mu\text{s}$, Duty Cycle $\angle 2.0\%$

(1) collector-Emitter voltage limited et $V_{CEci} = V_{\text{rated}}$ by an auxiliary circuit

MECHANICAL DATA CASE TO-3

DIMENSIONS		
	mm	inches
A	25,51	1,004
B	38,93	1,53
C	30,12	1,18
D	17,25	0,68
E	10,89	0,43
G	11,62	0,46
H	8,54	0,34
L	1,55	0,6
M	19,47	0,77
N	1	0,04
P	4,06	0,16



Pin 1 :	Base
Pin 2 :	Collector
Case :	Emitter